



RF Low Noise FET CE3520K3

20 / 24 GHz Super Low Noise FET in Hollow Plastic PKG

DESCRIPTION

- Super Low Noise and High Gain
- Hollow (Air cavity) Plastic package

FEATURES

- Super Low noise figure and high associated gain:

NF = 0.55 dB TYP., Ga = 13.8 dB TYP.

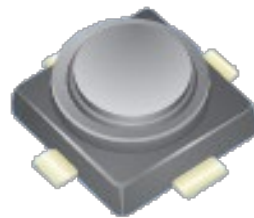
@V_{DS} = 2 V, I_D = 10 mA, f = 20 GHz

NF = 0.80 dB TYP., Ga = 13.9 dB TYP.

@V_{DS} = 2 V, I_D = 10 mA, f = 24 GHz

PACKAGE

- Micro-X plastic package



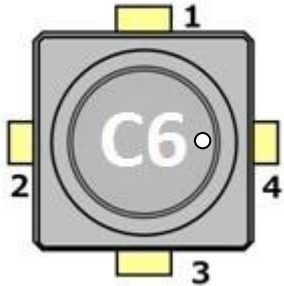
APPLICATIONS

- K-Band LNB (Low Noise Block)
- Doppler Sensor
- Low Noise Amplifier for microwave communication systems

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Description
CE3520K3	CE3520K3-C1	Micro-X plastic package	C6	<ul style="list-style-type: none"> • Embossed tape 8 mm wide • Pin 4 (Gate) faces the perforation side of the tape • MOQ 10k pcs/reel

PIN CONFIGURATION AND INTERNAL BLOCK DIAGRAM



Pin No.	Pin Name
1	Source
2	Drain
3	Source
4	Gate

ABSOLUTE MAXIMUM RATINGS

(TA = +25°C, unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain to Source Voltage	V_{DS}	4.0	V
Gate to Source Voltage	V_{GS}	-3.0	V
Drain Current	I_D	I_{DSS}	mA
Gate Current	I_G	80	μA
Total Power Dissipation	P_{tot}	125	mW
Channel Temperature	T_{ch}	+150	°C
Storage Temperature	T_{stg}	-55 to +125	°C
Operation Temperature	T_{op}	-55 to +125 ^{Note}	°C

Note Refer to Total Power Dissipation vs. Ambient Temperature graph on page 4

RECOMMENDED OPERATING RANGE

(TA = +25°C, unless otherwise specified)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V_{DS}	+1	+2	+3	V
Drain Current	I_D	5	10	15	mA

ELECTRICAL CHARACTERISTICS

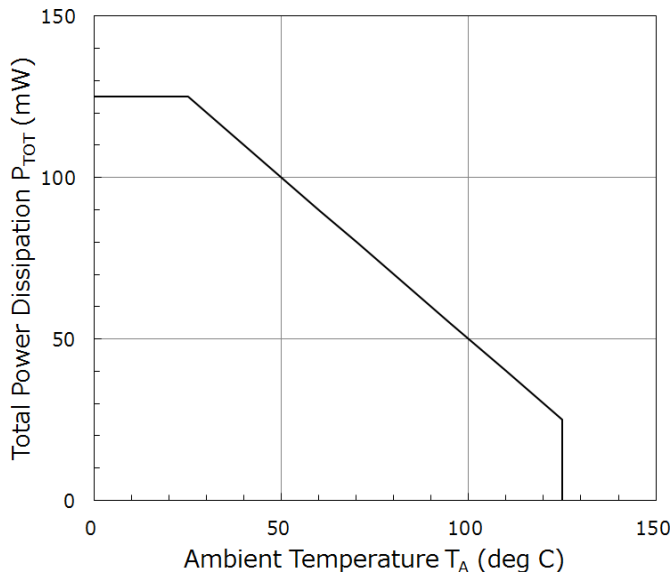
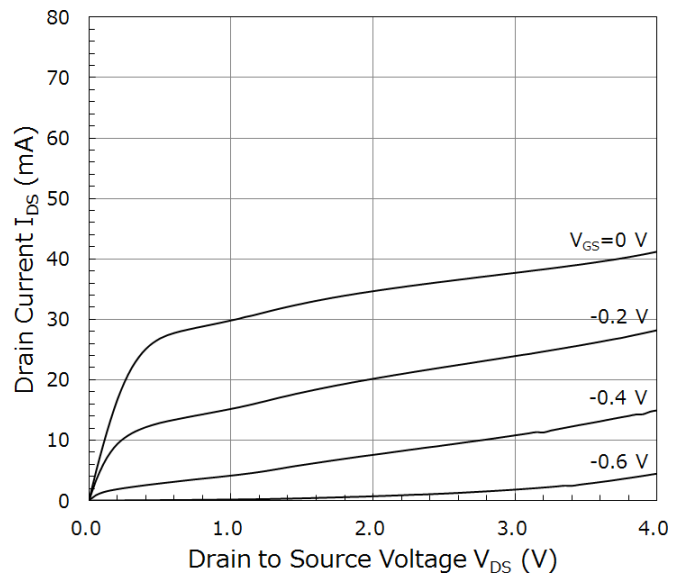
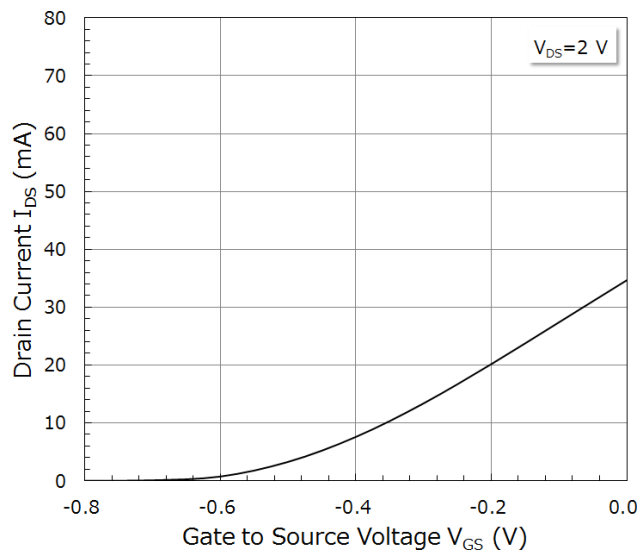
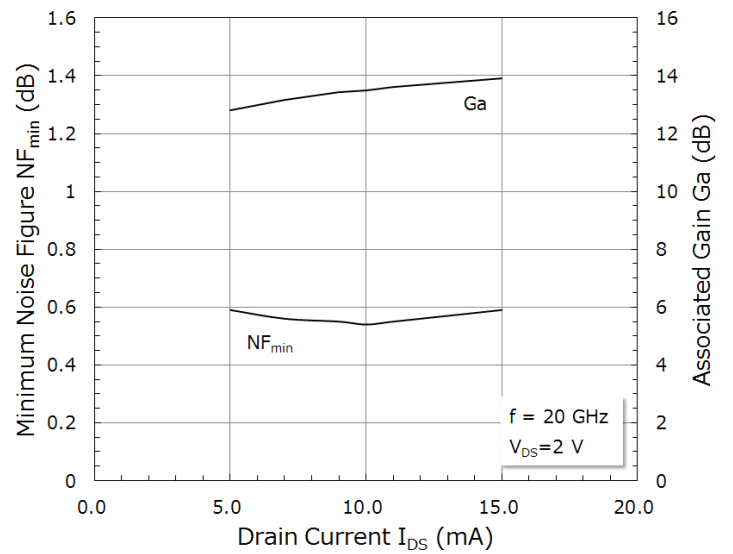
(TA = +25°C, unless otherwise specified)

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	I_{GSO}	$V_{GS} = -3.0V$	-	0.4	10	μA
Saturated Drain Current	I_{DSS}	$V_{DS} = 2V, V_{GS} = 0V$	23.0	40.0	57.0	mA
Gate to Source Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = 2V, I_D = 100\mu A$	-1.10	-0.75	-0.39	V
Transconductance	G_m	$V_{DS} = 2V, I_D = 10mA$	47.0	62.0	-	mS
Noise Figure ¹	NF	$V_{DS} = 2V, I_D = 10mA,$ $f = 20GHz$	-	0.55	0.80	dB
Associated Gain ¹	Ga		11.5	13.8	-	dB
Noise Figure ²	NF	$V_{DS} = 2V, I_D = 10mA,$ $f = 24GHz$	-	0.80	1.30	dB
Associated Gain ²	Ga		11.5	13.9	-	dB

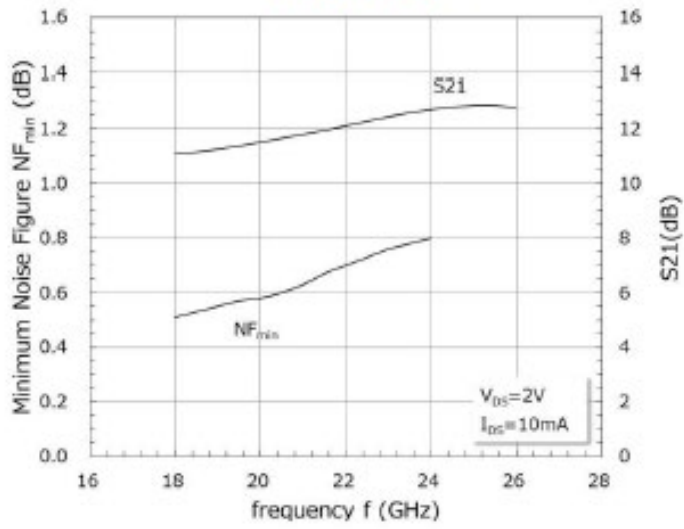
1. 100% tested on production devices
2. Not tested on production devices

TYPICAL CHARACTERISTICS:

(TA=+25°C, unless otherwise specified)

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE

DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

DRAIN CURRENT vs. GATE TO SOURCE VOLTAGE

MINIMUM NOISE FIGURE & ASSOCIATED GAIN vs. DRAIN CURRENT


MINIMUM NOISE FIGURE/ S21 vs. FREQUENCY



S-PARAMETERS

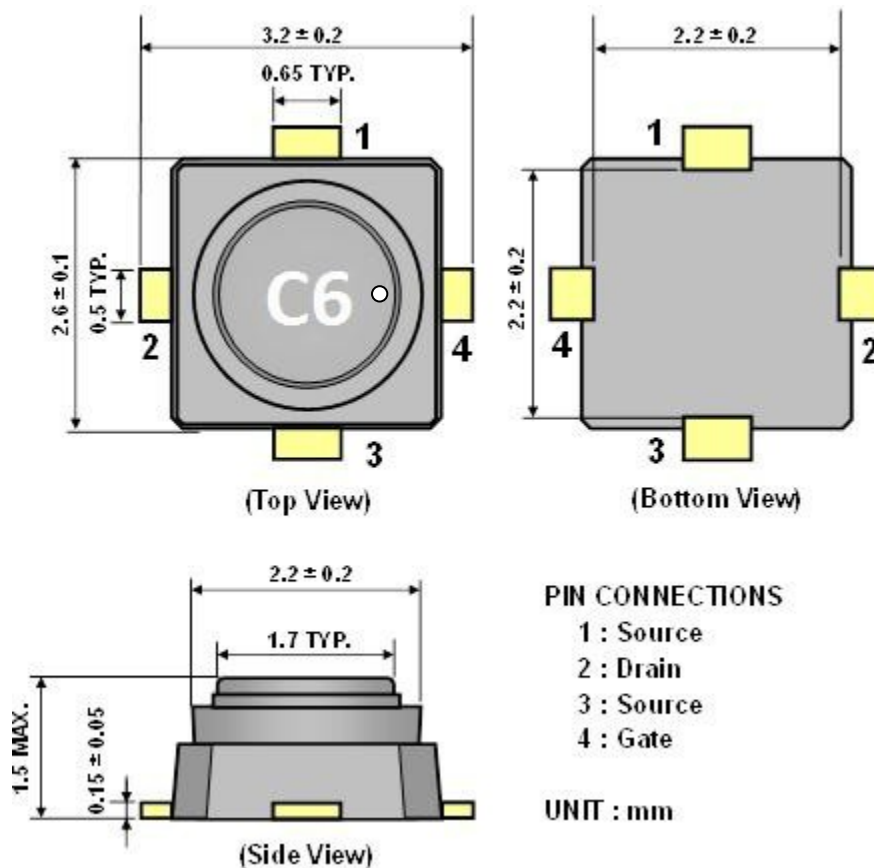
S-Parameters are available on the CEL web site.

RECOMMENDED SOLDERING CONDITIONS

Recommended Soldering Conditions are provided on the CEL web site.

PACKAGE DIMENSIONS

Micro-X plastic package



REVISION HISTORY

Version	Change to current version	Page(s)
CDS-0019-03 (Issue A) February 12, 2016	Initial datasheet	N/A
CDS-0019-03 (Issue B) April 27, 2016	Updated Marking Information	1, 2, 3
CDS-0019-04 (Issue A) July 29, 2016	Updated Specs in "Absolute Maximum Ratings" Table Added "Typical Characteristics" section (graphs) Added "S-Parameters" and "Recommended Soldering Conditions" sections	2, 4, 6
CDS-0019-04 (Issue B) Dec 04, 2018	Updated Applications Updated marking by adding a dot to the package Gate	1, 2, 6
CDS-0019-04 (Issue C) July 02, 2019	Added 24GHz Electrical and Typical Characteristics	1,3, 5

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